

Low Noise, High Performance, Quad Operational Amplifier

July 1994

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Low Input Noise Voltage Density at 1kHz. . $6\text{nV}/\sqrt{\text{Hz}}$ (Max)
 $4.3\text{nV}/\sqrt{\text{Hz}}$ (Typ)
- Slew Rate $1\text{V}/\mu\text{s}$ (Min)
 $3\text{V}/\mu\text{s}$ (Typ)
- Unity Gain Bandwidth 8MHz (Typ)
- High Open Loop Gain (Full Temp) $100\text{kV}/\text{V}$ (Min)
 $250\text{kV}/\text{V}$ (Typ)
- High CMRR, PSRR (Full Temp)..... 86dB (Min)
 100dB (Typ)
- Low Offset Voltage Drift $3\mu\text{V}/^\circ\text{C}$ (Typ)
- No Crossover Distortion
- Standard Quad Pinout

Applications

- High Q Active Filters
- Audio Amplifiers
- Integrators
- Signal Generators
- Instrumentation Amplifiers

Description

Low noise and high performance are key words describing the unity gain stable HA-5104/883. This general purpose quad amplifier offers an array of dynamic specifications including $1\text{V}/\mu\text{s}$ slew rate (min), and 8MHz bandwidth (typ). Complementing these outstanding parameters are very low noise specifications of $4.3\text{nV}/\sqrt{\text{Hz}}$ at 1kHz (typ) or $6\text{nV}/\sqrt{\text{Hz}}$ (max).

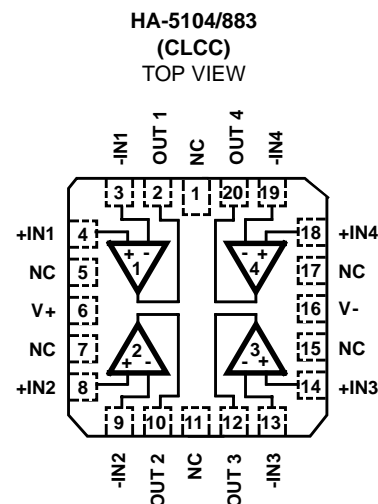
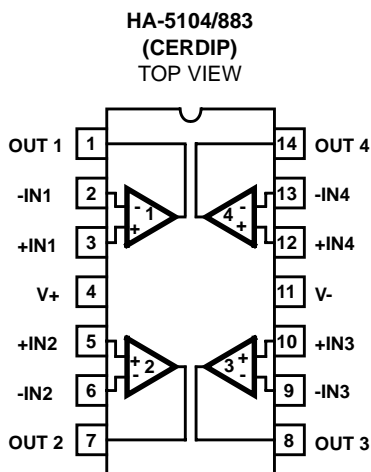
Fabricated using the Intersil standard high frequency D.I. process, these operational amplifiers also offer excellent input specifications such as 2.5mV (max) offset voltage and 75nA (max) offset current. Complementing these specifications are 100dB (min) open loop gain and 55dB channel separation (min). Economically, the HA-5104/883 also consumes a very moderate amount of power (225mW per package) while also saving board space and cost.

This impressive combination of features make this amplifier ideally suited for designs ranging from audio amplifiers and active filters to the most demanding signal conditioning and instrumentation circuits.

Ordering Information

| PART NUMBER | TEMPERATURE RANGE | PACKAGE |
|--------------|---|---------------------|
| HA1-5104/883 | -55°C to $+125^\circ\text{C}$ | 14 Lead CerDIP |
| HA4-5104/883 | -55°C to $+125^\circ\text{C}$ | 20 Lead Ceramic LCC |

Pinouts



Specifications HA5104/883

Absolute Maximum Ratings

| | |
|--|---|
| Voltage Between V+ and V- Terminals | 40V |
| Differential Input Voltage | 7V |
| Voltage at Either Input Terminal | V+ to V- |
| Peak Output Current | Indefinite (One Amplifier Shorted to Ground) |
| Junction Temperature (T _J) | +175°C |
| Storage Temperature Range | -65°C to +150°C |
| ESD Rating | <2000V |
| Lead Temperature (Soldering 10s) | +300°C |

Thermal Information

| | | |
|--|---------------|---------------|
| Thermal Resistance | θ_{JA} | θ_{JC} |
| CerDIP Package | 75°C/W | 20°C/W |
| Ceramic LCC Package | 65°C/W | 15°C/W |
| Package Power Dissipation Limit at +75°C for T _J ≤ +175°C | | |
| CerDIP Package | 1.33W | |
| Ceramic LCC Package | 1.54W | |
| Package Power Dissipation Derating Factor Above +75°C | | |
| CerDIP Package | 13.3mW/°C | |
| Ceramic LCC Package | 15.4mW/°C | |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

| | | |
|-----------------------------|-----------------|-------------------------------|
| Operating Temperature Range | -55°C to +125°C | $V_{INCM} \leq 1/2 (V+ - V-)$ |
| Operating Supply Voltage | ±5V to ±15V | $R_L \geq 2k\Omega$ |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: V_{SUPPLY} = ±15V, R_{SOURCE} = 100Ω, R_{LOAD} = 500kΩ, V_{OUT} = 0V, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | GROUP A SUBGROUPS | TEMPERATURE | LIMITS | | UNITS |
|-----------------------------|-------------------|---|-------------------|---------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Input Offset Voltage | V _{IO} | V _{CM} = 0V | 1 | +25°C | -2.5 | 2.5 | mV |
| | | | 2, 3 | +125°C, -55°C | -3.0 | 3.0 | mV |
| Input Bias Current | +I _B | V _{CM} = 0V, +R _S = 10kΩ, -R _S = 100kΩ | 1 | +25°C | -200 | 200 | nA |
| | | | 2, 3 | +125°C, -55°C | -325 | 325 | nA |
| | -I _B | V _{CM} = 0V, +R _S = 100kΩ, -R _S = 10kΩ | 1 | +25°C | -200 | 200 | nA |
| | | | 2, 3 | +125°C, -55°C | -325 | 325 | nA |
| Input Offset Current | I _{IO} | V _{CM} = 0V, +R _S = 10kΩ, -R _S = 10kΩ | 1 | +25°C | -75 | 75 | nA |
| | | | 2, 3 | +125°C, -55°C | -125 | 125 | nA |
| Common Mode Range | +CMR | V+ = +3V, V- = -27V | 1 | +25°C | +12 | - | V |
| | | | 2, 3 | +125°C, -55°C | +12 | - | V |
| | -CMR | V+ = +27V, V- = -3V | 1 | +25°C | - | -12 | V |
| | | | 2, 3 | +125°C, -55°C | - | -12 | V |
| Large Signal Voltage Gain | +A _{VOL} | V _{OUT} = 0V and +10V, R _L = 2kΩ | 4 | +25°C | 100 | - | kV/V |
| | | | 5, 6 | +125°C, -55°C | 100 | - | kV/V |
| | -A _{VOL} | V _{OUT} = 0V and -10V, R _L = 2kΩ | 4 | +25°C | 100 | - | kV/V |
| | | | 5, 6 | +125°C, -55°C | 100 | - | kV/V |
| Common Mode Rejection Ratio | +CMRR | ΔV _{CM} = +5V, V+ = +10V, V- = -20V, V _{OUT} = -5V | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 86 | - | dB |
| | -CMRR | ΔV _{CM} = -5V, V+ = +20V, V- = -10V, V _{OUT} = +5V | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 86 | - | dB |

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TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 500k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | GROUP A SUBGROUPS | TEMPERATURE | LIMITS | | UNITS |
|--------------------------------|-----------------------|--|----------------------|---------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Output Voltage Swing | +V _{OUT1} | R _L = 2kΩ | 1 | +25°C | 10 | - | V |
| | | | 2, 3 | +125°C, -55°C | 10 | - | V |
| | -V _{OUT1} | R _L = 2kΩ | 1 | +25°C | - | -10 | V |
| | | | 2, 3 | +125°C, -55°C | - | -10 | V |
| | +V _{OUT2} | R _L = 10kΩ | 1 | +25°C | 12 | - | V |
| | | | 2, 3 | +125°C, -55°C | 12 | - | V |
| -V _{OUT2} | R _L = 10kΩ | 1 | +25°C | - | -12 | V | |
| | | 2, 3 | +125°C, -55°C | - | -12 | V | |
| Output Current | +I _{OUT} | V _{OUT} = -5V | 1 | +25°C | 10 | - | mA |
| | | | 2, 3 | +125°C, -55°C | 10 | - | mA |
| | -I _{OUT} | V _{OUT} = +5V | 1 | +25°C | - | -10 | mA |
| | | | 2, 3 | +125°C, -55°C | - | -10 | mA |
| Quiescent Power Supply Current | +I _{CC} | V _{OUT} = 0V, I _{OUT} = 0mA | 1 | +25°C | - | 6.5 | mA |
| | | | 2, 3 | +125°C, -55°C | - | 7.5 | mA |
| | -I _{CC} | V _{OUT} = 0V, I _{OUT} = 0mA | 1 | +25°C | -6.5 | - | mA |
| | | | 2, 3 | +125°C, -55°C | -7.5 | - | mA |
| Power Supply Rejection Ratio | +PSRR | ΔV _{SUP} = 10V, V+ = +10V, V- = -15V V+ = +20V, V- = -15V | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 86 | - | dB |
| | -PSRR | ΔV _{SUP} = 10V, V+ = +15V, V- = -10V V+ = +15V, V- = -20V | 1 | +25°C | 86 | - | dB |
| | | | 2, 3 | +125°C, -55°C | 86 | - | dB |

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 2k\Omega$, $C_{LOAD} = 50pF$, $A_{VCL} = +1V/V$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | GROUP A SUBGROUPS | TEMPERATURE | LIMITS | | UNITS |
|--------------------|----------------|--|----------------------|-------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Slew Rate | +SR | V _{OUT} = -3V to +3V | 4 | +25°C | 1 | - | V/μs |
| | -SR | V _{OUT} = +3V to -3V | 4 | +25°C | 1 | - | V/μs |
| Rise and Fall Time | T _R | V _{OUT} = 0 to +200mV 10% ≤ T _R ≤ 90% | 4 | +25°C | - | 200 | ns |
| | T _F | V _{OUT} = 0 to -200mV 10% ≤ T _F ≤ 90% | 4 | +25°C | - | 200 | ns |
| Overshoot | +OS | V _{OUT} = 0 to +200mV | 4 | +25°C | - | 35 | % |
| | -OS | V _{OUT} = 0 to -200mV | 4 | +25°C | - | 35 | % |

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TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_{LOAD} = 2k\Omega$, $C_{LOAD} = 50pF$, $A_{VCL} = 1V/V$, Unless Otherwise Specified.

| PARAMETERS | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | LIMITS | | UNITS |
|---------------------------------|-----------|--|-------|-----------------|--------|-----|-----------------|
| | | | | | MIN | MAX | |
| Differential Input Resistance | R_{IN} | $V_{CM} = 0V$ | 1 | +25°C | 250 | - | k Ω |
| Input Noise Voltage Density | E_N | $R_S = 20\Omega$, $f_O = 1000Hz$ | 1 | +25°C | - | 6 | nV/ \sqrt{Hz} |
| Input Noise Current Density | I_N | $R_S = 2M\Omega$, $f_O = 1000Hz$ | 1 | +25°C | - | 3 | pA/ \sqrt{Hz} |
| Full Power Bandwidth | FPBW | $V_{PEAK} = 10V$ | 1, 2 | +25°C | 32 | - | kHz |
| Minimum Closed Loop Stable Gain | CLSG | $R_L = 2k\Omega$, $C_L = 50pF$ | 1 | -55°C to +125°C | +1 | - | V/V |
| Output Resistance | R_{OUT} | Open Loop | 1 | +25°C | - | 270 | Ω |
| Quiescent Power Consumption | PC | $V_{OUT} = 0V$, $I_{OUT} = 0mA$ | 1, 3 | -55°C to +125°C | - | 225 | mW |
| Channel Separation | CS | $R_S = 1k\Omega$, $A_{VCL} = 100V/V$, $V_{IN} = 100mV_{PEAK}$ at 10kHz Referred to Input | 1 | +25°C | 55 | - | dB |

NOTES:

- Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.
- Full Power Bandwidth guarantee based on Slew Rate measurement using $FPBW = Slew\ Rate / (2\pi V_{PEAK})$.
- Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on outputs.)

TABLE 4. ELECTRICAL TEST REQUIREMENTS

| MIL-STD-883 TEST REQUIREMENTS | SUBGROUPS (SEE TABLES 1 AND 2) |
|---|--------------------------------|
| Interim Electrical Parameters (Pre Burn-In) | 1 |
| Final Electrical Test Parameters | 1 (Note 1), 2, 3, 4, 5, 6 |
| Group A Test Requirements | 1, 2, 3, 4, 5, 6 |
| Groups C and D Endpoints | 1 |

NOTE:

- PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:

95 x 99 x 19 mils ± 1 mils
 2420 x 2530 x 483µm ± 25.4µm

METALLIZATION:

Type: Al, 1% Cu
 Thickness: 16kÅ ± 2kÅ

GLASSIVATION:

Type: Nitride (Si3N4) over Silox (SiO2, 5% Phos.)
 Silox Thickness: 12kÅ ± 2kÅ
 Nitride Thickness: 3.5kÅ ± 1.5kÅ

WORST CASE CURRENT DENSITY:

1.43 x 10⁵ A/cm²

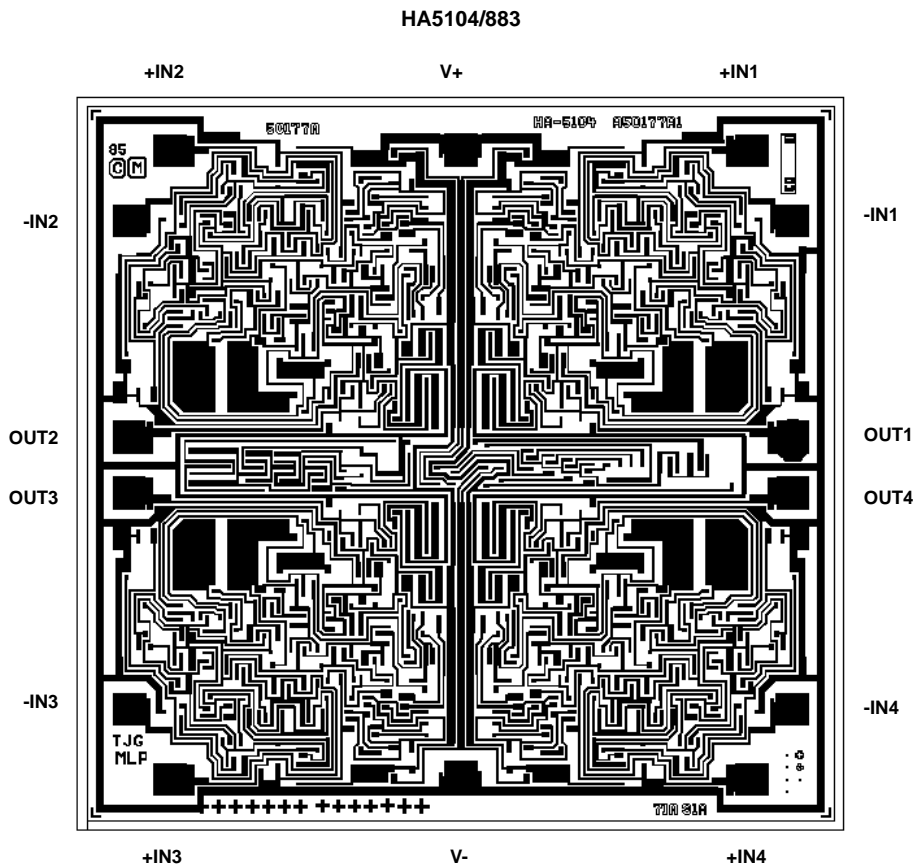
SUBSTRATE POTENTIAL (Powered Up):

Unbiased

TRANSISTOR COUNT: 175

PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout



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